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Iacopi is an associate professor at the Queensland Micro- and Nanotechnology Centre, Griffith University. She received her MSc degree in physics from Roma La Sapienza University, Italy, and her PhD degree in electrical engineering/materials science from the Katholieke Universiteit Leuven, Belgium (2004). She has 15 years of academic and industrial

experience in materials and processes for semiconductor technologies across devices, interconnects, packaging, and heterogeneous integration. Previously, she worked at the Interuniversity Microelectronics Center, Belgium, and the University of Tokyo, Japan. She directed the chip-package interaction strategy for GLOBALFOUNDRIES, USA, from 2010 to 2011. She has seven patents and over 100 publications. Iacopi was a recipient of a Gold Graduate Student Award from MRS in 2003, a Future Fellowship from the Australian Research Council in 2012, and a Global Innovation Award at the TechConnect Summit in Washington, DC, in 2014.



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Van Hove is a senior researcher in GaN power electronics with the Interuniversity Microelectronics Centre (IMEC). She obtained her degree in physics in 1980 from the Catholic University of Louvain, Belgium where she continued research at the Physics Department's Institute of Nuclear and Radiation Physics. She obtained her PhD degree and joined IMEC in

1985. She specialized in GaAs and InP III–V processing between 1986 and 1997. After that, she coordinated complementary metal oxide semiconductor (CMOS) back-end integration at IMEC. At the end of 2006, Van Hove returned to III–V research, focusing on research and development of CMOS-compatible GaN-on-Si power switching devices.



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Charles has been with CEA-LETI since 2010. He received his undergraduate and doctorate degrees at the University of Cambridge, where he began studying gallium nitride growth on silicon. Following this, he spent nearly five years at AIXTRON, where he worked with GaN, GaAs, and ZnO while demonstrating the performance

of metal–organic chemical vapor deposition tools. At CEA-LETI, he is in charge of 200-mm GaN silicon epitaxy, helping to develop and industrialize high-electron-mobility transistors using GaN on silicon substrates using the 200-mm CMOS transistor cleanroom facility, including performing epitaxy on a fully automated AIXTRON tool.



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His interests include synthesis, processing, and

characterization of thin films, heterostructures, and single crystals; device fabrication and physics (e.g., THz devices based on high Tc superconductors); and perovskites, SiC, chalcogenides, and CFRP. Endo has been involved in a multiyear National Project on Environment-Resistant Devices based on SiC in the Government Planning Office. He has published over 250 papers and presented more than 50 invited talks. He is a recipient of an Excellent Research Achievement Award from the Electrotechnical Laboratory.



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Aminbeidokhti is a PhD degree candidate at Queensland Micro- and Nanotechnology Centre, Griffith University. He received his BEng degree in 2009 and MEng degree in 2011 in electronic engineering from Semnan University, Iran. His research interests include power and high-frequency semiconductor devices. He is currently

working on the design, fabrication, characterization, analysis, and modeling of GaN-based high-electron-mobility transistors for power switching applications.



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Bahat-Treidel joined Ferdinand-Braun-Institut, Leibniz Institut für Höchstfrequenztechnik in 2006 for the development GaN switching transistors for high-voltage power applications. He holds a BSc degree in chemical engineering (2004) and a MSc degree in electro-optic engineering (1996) from Ben-Gurion University of the Negev, Israel. He received his PhD degree in

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Frank Brunner

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Brunner is responsible for epitaxy of GaN-based microwave transistors at the Ferdinand-Braun-Institut (FBH) since 2005. Additionally, he is in charge of the design and development of (Al,Ga)N-related optoelectronic device structures. He received his PhD degree in electrical engineering from the University of Karlsruhe, Germany, in 2002. His PhD work involved development of

MOVPE growth processes for GaAs-based heterojunction bipolar transistors. His postdoctoral work at FBH was comprised of optimization of epitaxial structures for InP-based high-frequency electronic devices. He is a shareholder of the GaN technology spin-off BeMiTec AG.



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Dimitrijević is a professor at Griffith University's School of Engineering and the deputy director of the Queensland Micro- and Nanotechnology Centre. He received his BEng (1982), MSci (1985), and PhD (1989) degrees in electronic engineering from the University of Nis, Yugoslavia. Prior to his present position, he was with the Semiconductor Factory of the Electronics Industry,

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Hilt is head of the GaN Power Electronics Group at Ferdinand-Braun-Institut (FBH), having joined FBH in 2006 for the development of GaN switching transistors for high-voltage power applications. He received his PhD degree in experimental physics in 1995 from the Free University of Berlin, Germany, for his work on the charge transport in liquefied rare gases, performed at the Hahn-Meitner-Institut Berlin,

Germany. Hilt analyzed charge transport in organic conductors and semiconductors for optoelectronic applications in The Netherlands at Technical University Delft and Leiden University. In 1999, he joined sglux GmbH, Germany, to develop ultraviolet photodiodes and became CEO in 2003.



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Kitabatake is with Panasonic's Device Solutions Center. He received his MSc degree in applied physics and PhD degree in engineering from Tohoku University, Japan. He has 34 years of industrial experience in materials, surface science, and semiconductor technologies across processing, device, and power electronics. Kitabatake has been directing a research group

developing an integrated evaluation platform for SiC epitaxial wafers in a Japanese national project for the past five years. He has published over 70 papers and holds over 60 Japanese and 60 US patents.



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Knauer has worked at the Ferdinand-Braun-Institut Berlin since 1992 on metal-organic vapor-phase epitaxy of (Al,Ga)(As,P)- and (Al,Ga,In)N-related device structures. He received a diploma in physics in 1981 from the State University of Chisinau, Moldova, for his work on the epitaxy and optical properties of ZnSe layers on sapphire. In 1981, he joined the Central

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the design and development of power heterojunction bipolar transistors and power GaN devices. From 1992 to 2007 he has been responsible for clean room technology and processing of electronic devices. He received his PhD degree in electrical engineering in 1989 at the Technical University of Darmstadt, Germany where he worked on the technology and design of high-temperature and high-power GaAs-based devices, and then developed micromechanical sensors based on III/V compound semiconductors as a postdoctoral researcher.



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